

NTP6N60

Preferred Device

Product Preview

Power MOSFET 6 Amps, 600 Volts N-Channel TO-220

Designed for high voltage, high speed switching applications in power supplies, converters, power motor controls and bridge circuits.

Features

- Higher Current Rating
- Lower $R_{DS(on)}$
- Lower Capacitances
- Lower Total Gate Charge
- Tighter V_{SD} Specifications
- Avalanche Energy Specified

Typical Applications

- Switch Mode Power Supplies
- PWM Motor Controls
- Converters
- Bridge Circuits

MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	600	Vdc
Drain-Gate Voltage ($R_{GS} = 1.0 \text{ M}\Omega$)	V_{DGR}	600	Vdc
Gate-Source Voltage	V_{GS}	± 20	Vdc
– Continuous	V_{GSM}	± 40	
– Non-Repetitive ($t_p \leq 10 \text{ ms}$)			
Drain	I_D	6.0	Adc
– Continuous	I_D	4.8	
– Continuous @ 100°C	I_{DM}	21	
– Single Pulse ($t_p \leq 10 \mu\text{s}$)			
Total Power Dissipation Derate above 25°C	P_D	142 1.14	Watts W/ $^\circ\text{C}$
Operating and Storage Temperature Range	T_J, T_{stg}	-55 to 150	$^\circ\text{C}$
Single Drain-to-Source Avalanche Energy – Starting $T_J = 25^\circ\text{C}$ ($V_{DD} = 100 \text{ V}$, $V_{GS} = 10 \text{ Vdc}$, $I_L = 6 \text{ A}$, $L = 25 \text{ mH}$, $R_G = 25 \Omega$)	E_{AS}	450	mJ
Thermal Resistance	$R_{\theta JC}$	0.88	$^\circ\text{C/W}$
– Junction-to-Case	$R_{\theta JA}$	62.5	
– Junction-to-Ambient	$R_{\theta JA}$	50	
– Junction-to-Ambient (Note 1.)			
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 10 seconds	T_L	260	$^\circ\text{C}$

1. When surface mounted to an FR4 board using the minimum recommended pad size.

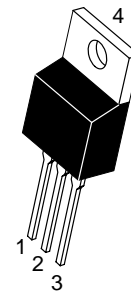
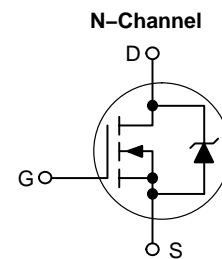
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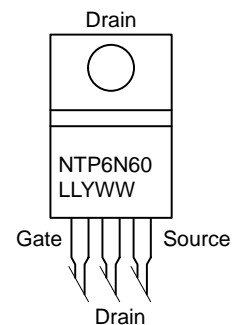
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V_{DSS}	$R_{DS(on)}$ TYP	I_D MAX
600 V	850 m Ω	6.0 A



TO-220AB
CASE 221A
STYLE 5

MARKING DIAGRAM & PIN ASSIGNMENT



NTP6N60 = Device Code
LL = Location Code
Y = Year
WW = Work Week

ORDERING INFORMATION

Device	Package	Shipping
NTP6N60	TO-220AB	50 Units/Rail

Preferred devices are recommended choices for future use and best overall value.

NTP6N60

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage (V _{GS} = 0 Vdc, I _D = 0.25 mAdc) Temperature Coefficient (Positive)	V _{(BR)DSS}	600 –	– 715	– –	Vdc mV/°C
Zero Gate Voltage Collector Current (V _{DS} = 600 Vdc, V _{GS} = 0 Vdc) (V _{DS} = 600 Vdc, V _{GS} = 0 Vdc, T _J = 125°C)	I _{DSS}	– –	– –	10 100	μAdc
Gate-Body Leakage Current (V _{GS} = ±20 Vdc, V _{DS} = 0)	I _{GSS(f)} I _{GSS(r)}	– –	– –	100 100	nAdc

ON CHARACTERISTICS (Note 2.)

Gate Threshold Voltage I _D = 0.25 mA, V _{DS} = V _{GS} Temperature Coefficient (Negative)	V _{GS(th)}	2.0 –	2.6 6.6	4.0 –	Vdc mV/°C
Static Drain-to-Source On-Resistance (V _{GS} = 10 Vdc, I _D = 3 Adc)	R _{DS(on)}	–	850	1200	mOhm
Drain-to-Source On-Voltage (V _{GS} = 10 Vdc, I _D = 6 Adc) (V _{GS} = 10 Vdc, I _D = 3 Adc, T _J = 125°C)	V _{DS(on)}	– –	– –	8.6 7.9	Vdc
Forward Transconductance (V _{DS} = 15 Vdc, I _D = 3 Adc)	g _{FS}	2.0	7.0	–	mhos

DYNAMIC CHARACTERISTICS

Input Capacitance	(V _{DS} = 25 Vdc, V _{GS} = 0 Vdc, f = 1.0 MHz)	C _{iss}	–	1190	1670	pF
Output Capacitance		C _{oss}	–	350	490	
Transfer Capacitance		C _{riss}	–	20	40	

SWITCHING CHARACTERISTICS (Note 3.)

Turn-On Delay Time	(V _{DD} = 300 Vdc, I _D = 6 Adc, V _{GS} = 10 Vdc, R _G = 9.1 Ω)	t _{d(on)}	–	11	20	ns
Rise Time		t _r	–	10	20	
Turn-Off Delay Time		t _{d(off)}	–	34	70	
Fall Time		t _f	–	19	40	
Gate Charge	(V _{DS} = 480 Vdc, I _D = 6 Adc, V _{GS} = 10 Vdc)	Q _T	–	24	30	nC
		Q ₁	–	6.0	–	
		Q ₂	–	8.0	–	
		Q ₃	–	12	–	

SOURCE-DRAIN DIODE CHARACTERISTICS

Forward On-Voltage (Note 2.)	(I _S = 6 Adc, V _{GS} = 0 Vdc) (I _S = 6 Adc, V _{GS} = 0 Vdc, T _J = 125°C)	V _{SD}	– –	0.85 0.73	1.0 –	Vdc
Reverse Recovery Time	(I _S = 6 Adc, V _{GS} = 0 Vdc, di _S /dt = 100 A/μs)	t _{rr}	–	440	–	ns
		t _a	–	130	–	
		t _b	–	310	–	
Reverse Recovery Stored Charge		Q _{RR}	–	2.8	–	μC

INTERNAL PACKAGE INDUCTANCE

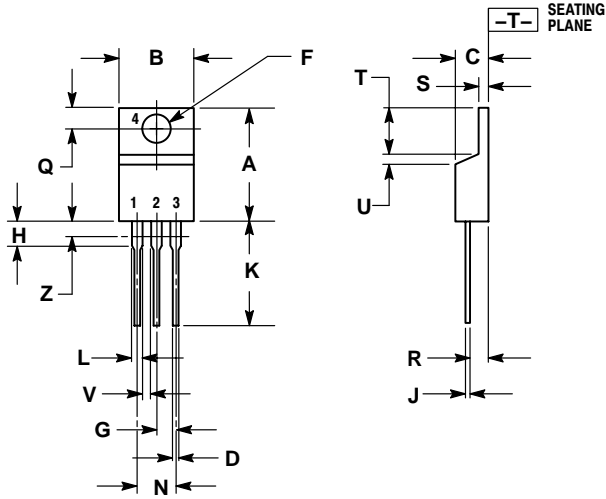
Internal Drain Inductance (Measured from contact screw on tab to center of die) (Measured from the drain lead 0.25" from package to center of die)	L _D	– –	3.5 4.5	– –	nH
Internal Source Inductance (Measured from the source lead 0.25" from package to source bond pad)	L _S	–	7.5	–	

- Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.
- Switching characteristics are independent of operating junction temperature.

NTP6N60

PACKAGE DIMENSIONS

TO-220 THREE-LEAD
TO-220AB
CASE 221A-09
ISSUE AA



NOTES:


1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.570	0.620	14.48	15.75
B	0.380	0.405	9.66	10.28
C	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.42	2.66
H	0.110	0.155	2.80	3.93
J	0.018	0.025	0.46	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	---	1.15	---
Z	---	0.080	---	2.04

STYLE 5:

- PIN 1. GATE
- DRAIN
- SOURCE
- DRAIN

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